MicroCapacitance (MC) SC *SIDACtor* Device

The DO-214AA SC MC *SIDACtor* series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance. C_O values for the MicroCapacitance device are 40% lower than a standard SC part.

This MC *SIDACtor* series is used to enable equipment to meet various regulatory requirements including GR 1089, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68). Contact factory regarding ITU K.20, K.21, and K.45.

Electrical Parameters

Part Number *	V_{DRM} Volts	V_S Volts	V_T Volts	I_{DRM} µAmps	I_S mAmps	I_T Amps	I_H mAmps	C_O pF
P0080SC MC **	6	25	4	5	800	2.2	50	55
P0300SC MC **	25	40	4	5	800	2.2	50	35
P0640SC MC	58	77	4	5	800	2.2	150	60
P0720SC MC	65	88	4	5	800	2.2	150	60
P0900SC MC	75	98	4	5	800	2.2	150	60
P1100SC MC	90	130	4	5	800	2.2	150	50
P1300SC MC	120	160	4	5	800	2.2	150	50
P1500SC MC	140	180	4	5	800	2.2	150	50
P1800SC MC	170	220	4	5	800	2.2	150	40
P2300SC MC	190	260	4	5	800	2.2	150	40
P2600SC MC	220	300	4	5	800	2.2	150	40
P3100SC MC	275	350	4	5	800	2.2	150	40
P3500SC MC	320	400	4	5	800	2.2	150	40

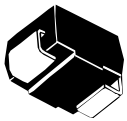
* For surge ratings, see table below.
** Contact factory for release date.

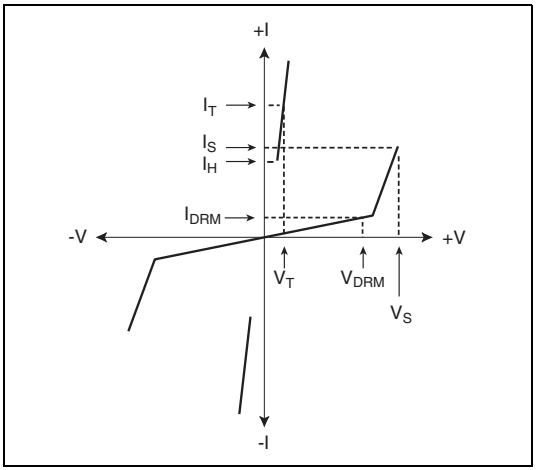
General Notes:
- All measurements are made at an ambient temperature of 25 °C. I_{PP} applies to -40 °C through +85 °C temperature range.
- I_{PP} is a repetitive surge rating and is guaranteed for the life of the product.
- Listed *SIDACtor* devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V_{DRM} is measured at I_{DRM}.
- V_S is measured at 100 V/µs.
- Special voltage (V_S and V_{DRM}) and holding current (I_H) requirements are available upon request.
- Off-state capacitance is measured at 1 MHz with a 2 V bias.

Surge Ratings

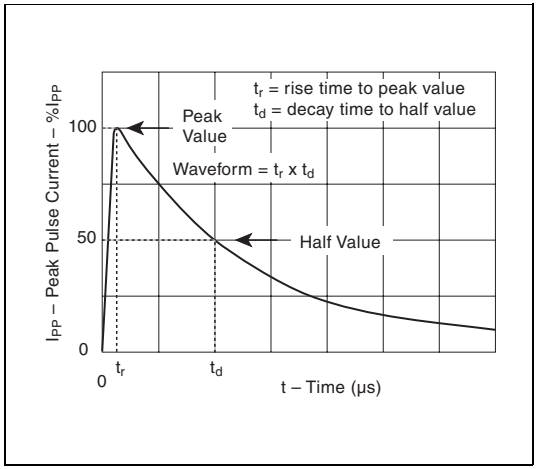
Series	I_{PP} 2x10 µs Amps	I_{PP} 8x20 µs Amps	I_{PP} 10x160 µs Amps	I_{PP} 10x560 µs Amps	I_{PP} 10x1000 µs Amps	I_{TSM} 60 Hz Amps	di/dt Amps/µs
C	500	400	200	150	100	30	500

Thermal Considerations

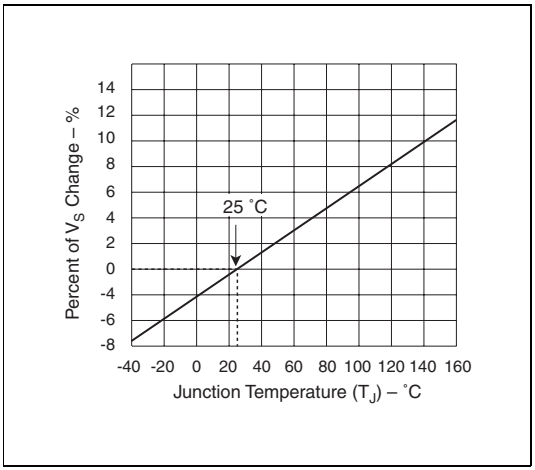
Package	Symbol	Parameter	Value	Unit
DO-214AA 	T_J	Operating Junction Temperature Range	-40 to +150	°C
	T_S	Storage Temperature Range	-65 to +150	°C
	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W



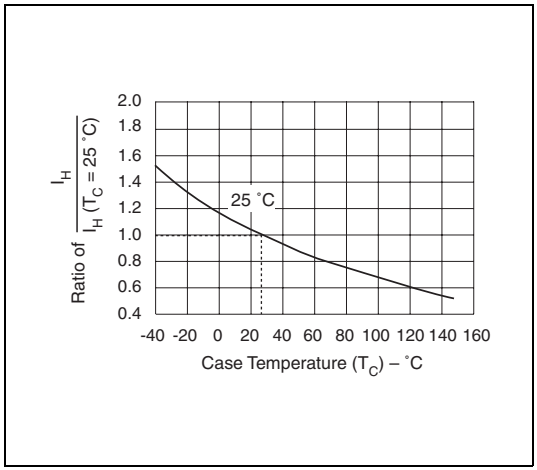
V-I Characteristics



t_r x t_d Pulse Wave-form



Normalized V_S Change versus Junction Temperature



Normalized DC Holding Current versus Case Temperature